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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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Dual P-Channel 30-V (D-S) MOSFET

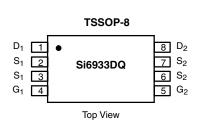
PRODUCT SUMMARY			
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)	
- 30	0.045 at V _{GS} = - 10 V	± 3.5	
	0.085 at V _{GS} = - 4.5 V	± 2.5	

FEATURES

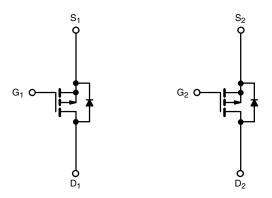
- Halogen-free
- TrenchFET® Power MOSFETs







Ordering Information: Si6933DQ-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	5 T _A = 25 °C, unles	ss otherwise n	oted		
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	- 30		
Gate-Source Voltage		V_{GS}	± 20	V	
Ocaliana Daria Ocana I/T 450 00\8	T _A = 25 °C	1	± 3.5		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C	I _D	± 2.8		
Pulsed Drain Current		I _{DM}	± 20	_ A	
Continuous Source Current (Diode Conduction) ^a		I _S	- 1.25		
	T _A = 25 °C	P _D	1.0	10/	
Maximum Power Dissipation ^a	T _A = 70 °C	r _D	0.64	W	
Operating Junction and Storage Temperature Range		T _J , T _{stq}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Maximum Junction-to-Ambient ^a	R _{thJA}	125	°C/W	

Notes:

a. Surface Mounted on FR4 board, $t \leq 10 \ s.$

For SPICE model information via the Worldwide Web: http://www.vishay.com/www/product/spice.htm.

Si6933DQ

Vishay Siliconix



SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions Min.		. Тур.	Max.	Unit		
Static								
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	- 1.0			V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA		
Zava Cata Valta na Duain Comunant	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V			- 1	μΑ		
Zero Gate Voltage Drain Current		V_{DS} = - 30 V, V_{GS} = 0 V, T_{J} = 55 °C			- 25			
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 15			Α		
Durin Course On Olate Desistence	B-ac	$V_{GS} = -10 \text{ V}, I_D = 3.5 \text{ A}$		0.035	0.045	0		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = 2.5 \text{ A}$		0.062	0.085	Ω		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 3.5 A		7.2		S		
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.25 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.77	- 1.2	V		
Dynamic ^b								
Total Gate Charge	Q_g			17	30			
Gate-Source Charge	Q _{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -3.5 \text{ A}$		4.4		nC		
Gate-Drain Charge	Q _{gd}			3.1				
Turn-On Delay Time	t _{d(on)}			13	20			
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		10	20			
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 10 V, R_G = 6 Ω		33	60	ns		
Fall Time	t _f			10	20			
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.25 A, dI/dt = 100 A/μs		30	60			

Notes:

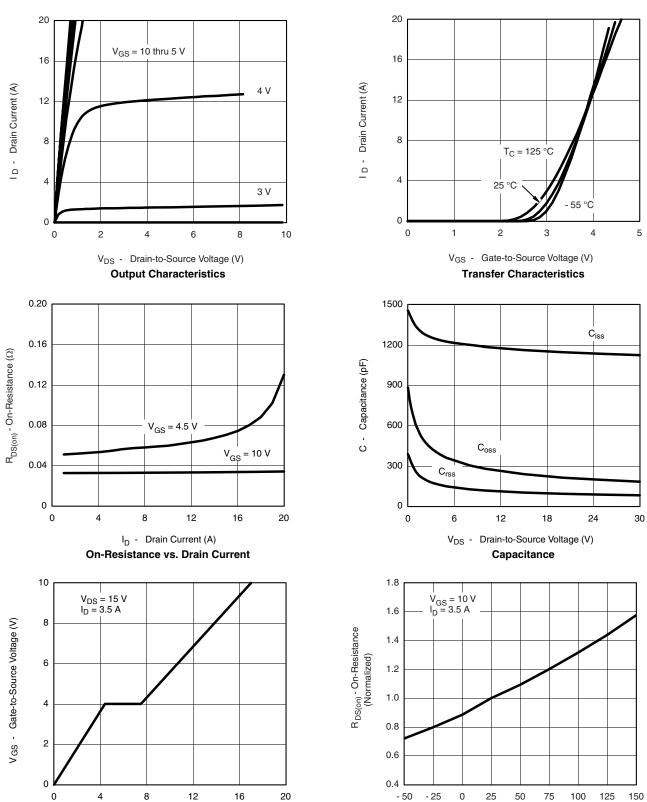
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Total Gate Charge (nC)

Gate Charge

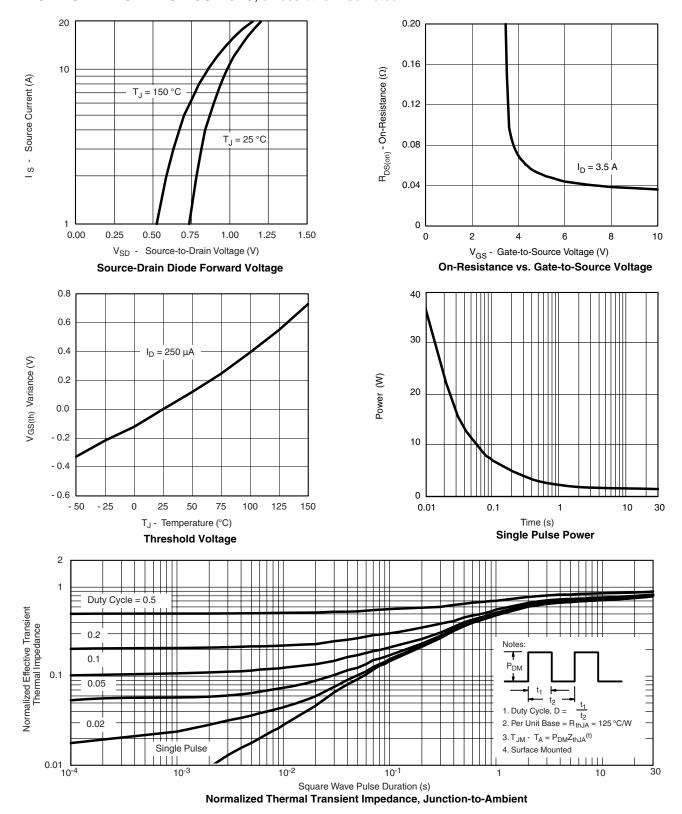
T_J - Junction Temperature (°C)

On-Resistance vs. Junction Temperature

Vishay Siliconix

VISHAY

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?70640.



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